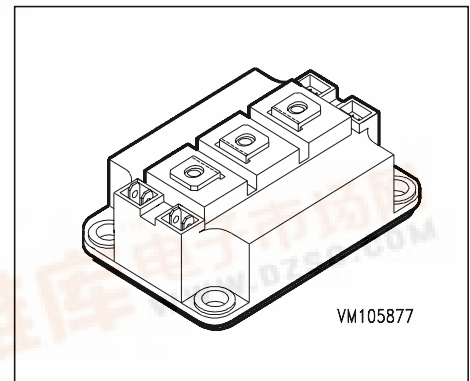


SIEMENS

BSM 200 GAL 120 DN2

IGBT Power Module

- Single switch with chopper diode
- Package with insulated metal base plate



| Type | V_{CE} | I_C | Package | Ordering Code |
|---------------------|----------|-------|-------------------|------------------|
| BSM 200 GAL 120 DN2 | 1200V | 290A | HALFBRIDGE GAL 2B | C67070-A2301-A70 |

Maximum Ratings

| Parameter | Symbol | Values | Unit |
|--|--------------|---------------|------------------|
| Collector-emitter voltage | V_{CE} | 1200 | V |
| Collector-gate voltage | V_{CGR} | 1200 | |
| $R_{GE} = 20 \text{ k}\Omega$ | | | |
| Gate-emitter voltage | V_{GE} | ± 20 | |
| DC collector current | I_C | 290 | A |
| $T_C = 25 \text{ }^\circ\text{C}$ | | | |
| $T_C = 80 \text{ }^\circ\text{C}$ | | 200 | |
| Pulsed collector current, $t_p = 1 \text{ ms}$ | I_{Cpuls} | 580 | |
| $T_C = 25 \text{ }^\circ\text{C}$ | | | |
| $T_C = 80 \text{ }^\circ\text{C}$ | | 400 | |
| Power dissipation per IGBT | P_{tot} | 1400 | W |
| $T_C = 25 \text{ }^\circ\text{C}$ | | | |
| Chip temperature | T_j | + 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 ... + 150 | |
| Thermal resistance, chip case | R_{thJC} | ≤ 0.09 | K/W |
| Diode thermal resistance, chip case | R_{thJCD} | - | |
| Diode thermal resistance, chip-case,chopper | R_{thJCDC} | ≤ 0.125 | |
| Insulation test voltage, $t = 1 \text{ min.}$ | V_{is} | 2500 | Vac |
| Creepage distance | - | 20 | mm |
| Clearance | - | 11 | |
| DIN humidity category, DIN 40 040 | - | F | - |
| IEC climatic category, DIN IEC 68-1 | - | 55 / 150 / 56 | |



Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|--|---------------|--------|------------|----------|------|
| | | min. | typ. | max. | |
| Static Characteristics | | | | | |
| Gate threshold voltage $V_{GE} = V_{CE}, I_C = 8\text{ mA}$ | $V_{GE(th)}$ | 4.5 | 5.5 | 6.5 | V |
| Collector-emitter saturation voltage $V_{GE} = 15\text{ V}, I_C = 200\text{ A}, T_j = 25\text{ °C}$ $V_{GE} = 15\text{ V}, I_C = 200\text{ A}, T_j = 125\text{ °C}$ | $V_{CE(sat)}$ | - - | 2.5 3.1 | 3 3.7 | |
| Zero gate voltage collector current $V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_j = 25\text{ °C}$ $V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_j = 125\text{ °C}$ | I_{CES} | - - | 3 12 | 4 - | mA |
| Gate-emitter leakage current $V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$ | I_{GES} | - | - | 400 | nA |
| AC Characteristics | | | | | |
| Transconductance $V_{CE} = 20\text{ V}, I_C = 200\text{ A}$ | g_{fs} | 108 | - | - | S |
| Input capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$ | C_{iss} | - | 13 | - | nF |
| Output capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$ | C_{oss} | - | 2 | - | |
| Reverse transfer capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$ | C_{rss} | - | 1 | - | |

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|-----------|--------|--------|------|------|------|
| | | min. | typ. | max. | |

Switching Characteristics, Inductive Load at $T_j = 125\text{ °C}$

| | | | | | |
|---|--------------|---|-----|-----|----|
| Turn-on delay time $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 200\text{ A}$ $R_{Gon} = 4.7\ \Omega$ | $t_{d(on)}$ | - | 110 | 220 | ns |
| Rise time $V_{CC} = 600\text{ V}$, $V_{GE} = 15\text{ V}$, $I_C = 200\text{ A}$ $R_{Gon} = 4.7\ \Omega$ | t_r | - | 80 | 160 | |
| Turn-off delay time $V_{CC} = 600\text{ V}$, $V_{GE} = -15\text{ V}$, $I_C = 200\text{ A}$ $R_{Goff} = 4.7\ \Omega$ | $t_{d(off)}$ | - | 550 | 800 | |
| Fall time $V_{CC} = 600\text{ V}$, $V_{GE} = -15\text{ V}$, $I_C = 200\text{ A}$ $R_{Goff} = 4.7\ \Omega$ | t_f | - | 80 | 120 | |

Free-Wheel Diode

| | | | | | |
|--|----------|---|---|---|---------------|
| Diode forward voltage $I_F = 200\text{ A}$, $V_{GE} = 0\text{ V}$, $T_j = 25\text{ °C}$ $I_F = 200\text{ A}$, $V_{GE} = 0\text{ V}$, $T_j = 125\text{ °C}$ | V_F | - | - | - | V |
| Reverse recovery time $I_F = 200\text{ A}$, $V_R = -600\text{ V}$, $V_{GE} = 0\text{ V}$ $di_F/dt = -2000\text{ A}/\mu\text{s}$, $T_j = 125\text{ °C}$ | t_{rr} | - | - | - | μs |
| Reverse recovery charge $I_F = 200\text{ A}$, $V_R = -600\text{ V}$, $V_{GE} = 0\text{ V}$ $di_F/dt = -2000\text{ A}/\mu\text{s}$ $T_j = 25\text{ °C}$ $T_j = 125\text{ °C}$ | Q_{rr} | - | - | - | μC |

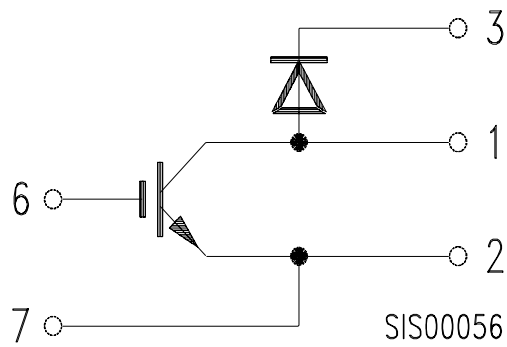
Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

| Parameter | Symbol | Values | | | Unit |
|-----------|--------|--------|------|------|------|
| | | min. | typ. | max. | |

Chopper Diode

| | | | | | |
|--|-----------|--------|------------|----------|---------------|
| Chopper diode forward voltage $I_{FC} = 300\text{ A}$, $V_{GE} = 0\text{ V}$, $T_j = 25\text{ °C}$ $I_{FC} = 300\text{ A}$, $V_{GE} = 0\text{ V}$, $T_j = 125\text{ °C}$ | V_{FC} | - - | 2.3 1.8 | 2.8 - | V |
| Reverse recovery time, chopper $I_{FC} = 300\text{ A}$, $V_R = -600\text{ V}$, $V_{GE} = 0\text{ V}$ $di_F/dt = -2500\text{ A}/\mu\text{s}$, $T_j = 25\text{ °C}$ | t_{rrC} | - | 500 | - | ns |
| Reverse recovery charge, chopper $I_{FC} = 300\text{ A}$, $V_R = -600\text{ V}$, $V_{GE} = 0\text{ V}$ $di_F/dt = -2500\text{ A}/\mu\text{s}$ $T_j = 25\text{ °C}$ $T_j = 125\text{ °C}$ | Q_{rrC} | - - | 14 40 | - - | μC |

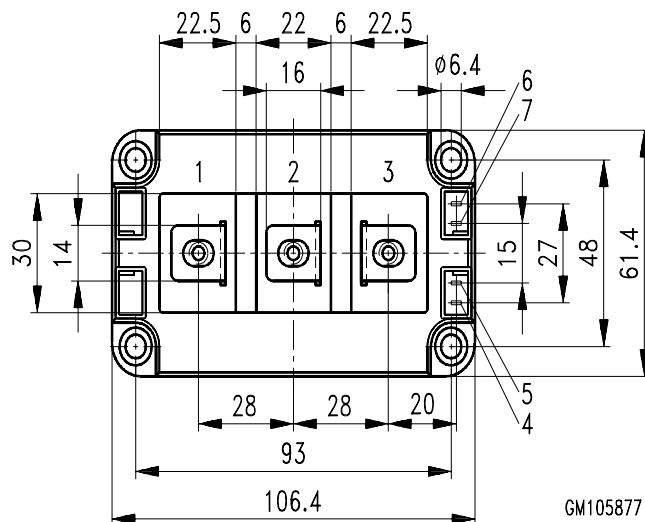
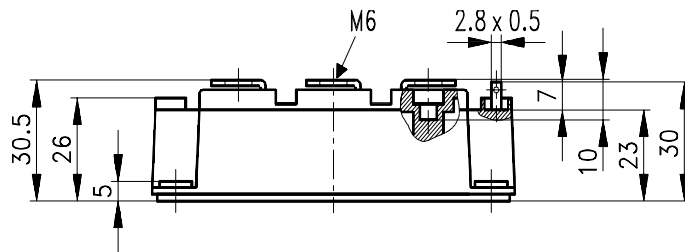
Circuit Diagram



Package Outlines

Dimensions in mm

Weight: 420 g



GM105877